

N-channel 100 V, 153 mΩ logic level MOSFET in LFPAK56 27 June 2014 Product data sheet

1. General description

Logic level N-channel MOSFET in an LFPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V_{GS(th)} rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Qui	ck reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	100	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>	-	-	9.4	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	-	37	W
Static charact	eristics					
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 2 A; T _j = 25 °C; <u>Fig. 11</u>	-	122	153	mΩ
Dynamic char	acteristics					
Q _{GD}	gate-drain charge	$V_{GS} = 5 \text{ V}; I_D = 2 \text{ A}; V_{DS} = 80 \text{ V};$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 13}}{\text{Fig. 14}}; \frac{\text{Fig. 14}}{\text{Fig. 14}}$	-	3.1	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source		
3	S	source	q	G-UFT 4
4	G	gate	មុប្បូប្	mbb076 S
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56; Power- SO8 (SOT669)	

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK9Y153-100E	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9Y153-100E	915310E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	100	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	100	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-10	10	V
		$T_j \le 175 \ ^{\circ}C; \ Pulsed$	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	37	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2</u>		-	9.4	А
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>		-	6.6	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3		-	38	А

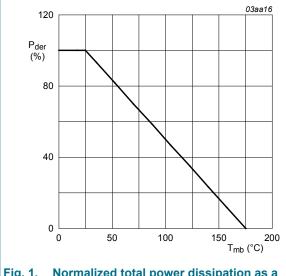
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Symbol	Parameter	Conditions		Min	Мах	Unit
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C		-	9.4	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^\circ C$		-	38	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 9.4 \text{ A}; \ V_{sup} \leq 100 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} &= 5 \text{ V}; \ T_{j(init)} = 25 \ ^\circ\text{C}; \ unclamped; \\ \hline Fig. \ 4 \end{split}$	[3][4]	-	9.5	mJ

- [1]
- Accumulated pulse duration up to 50 hours delivers zero defect ppm Significantly longer life times are achieved by lowering $\rm T_{j}$ and or $\rm V_{GS}$ [2]
- Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [3]
- Refer to application note AN10273 for further information. [4]





$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ C)}} \times 100 \%$$

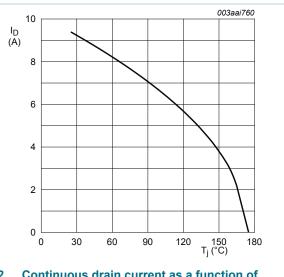
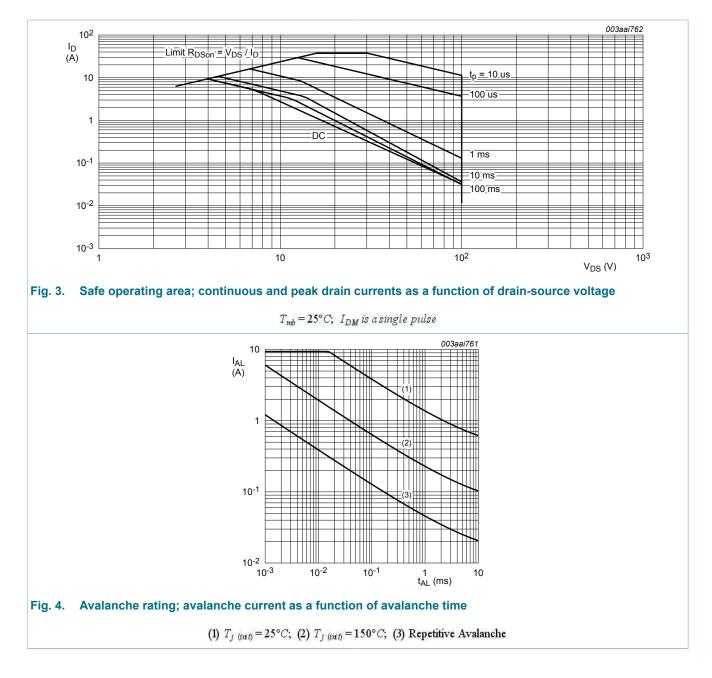


Fig. 2. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 5V$

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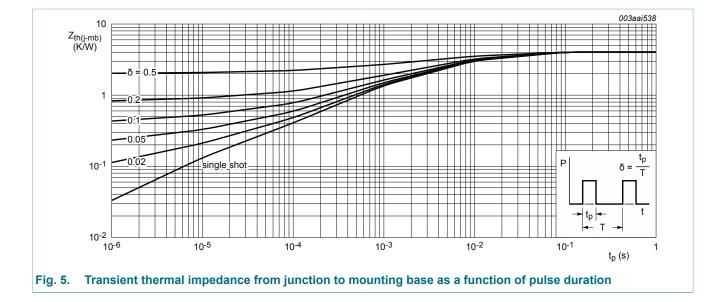
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9. Thermal characteristics

Table 6. The	rmal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	4.03	K/W

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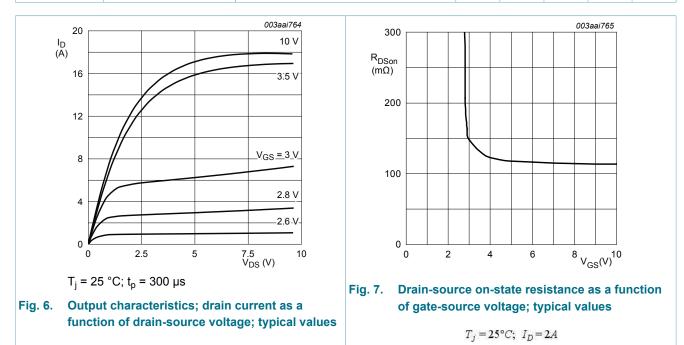
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics	· · ·				
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	90	-	-	V
	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	1.4	1.7	2.1	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	2.45	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 9	0.5	-	-	V
I _{DSS} drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	1	μA	
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
GSS gate leakage current	V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA	
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V_{GS} = 5 V; I _D = 2 A; T _j = 25 °C; <u>Fig. 11</u>	-	122	153	mΩ
	resistance	V _{GS} = 10 V; I _D = 2 A; T _j = 25 °C; <u>Fig. 11</u>	-	117	146	mΩ
		V _{GS} = 5 V; I _D = 2 A; T _j = 175 °C; Fig. 12; Fig. 11	-	-	422	mΩ
Dynamic cl	haracteristics	· · · ·	1			
Q _{G(tot)}	total gate charge	I _D = 2 A; V _{DS} = 80 V; V _{GS} = 5 V;	-	6.8	-	nC
Q _{GS}	Q_{GS} gate-source charge $T_j = 25 \text{ °C}; \text{ Fig. 1}$	T _j = 25 °C; <u>Fig. 13; Fig. 14</u>	-	1.1	-	nC
Q _{GD}	gate-drain charge		-	3.1	-	nC

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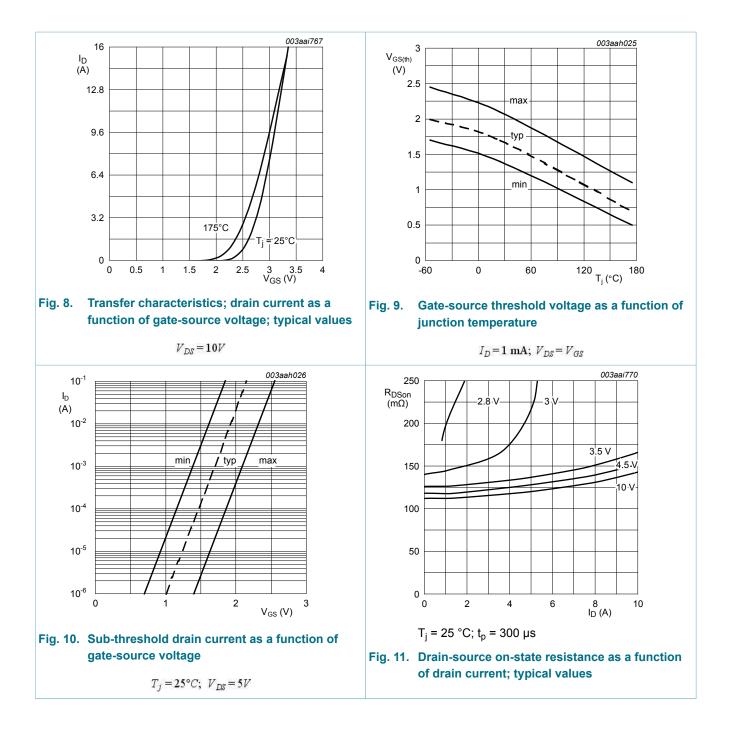
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;		-	537	716	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	59	71	pF
C _{rss}	reverse transfer capacitance			-	46	63	pF
t _{d(on)}	turn-on delay time	V_{DS} = 80 V; R _L = 10 Ω; V _{GS} = 5 V; R _{G(ext)} = 5 Ω; T _j = 25 °C		-	6	-	ns
t _r	rise time			-	10.9	-	ns
t _{d(off)}	turn-off delay time			-	10	-	ns
t _f	fall time			-	7.9	-	ns
Source-dra	ain diode	-	1	1	1		
V _{SD}	source-drain voltage	I_{S} = 2 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 16</u>		-	0.81	1.2	V
t _{rr}	reverse recovery time	I _S = 2 A; dI _S /dt = -100 A/μs; V _{GS} = 0 V;		-	26	-	ns
Q _r	recovered charge	V _{DS} = 25 V; T _j = 25 °C		-	28	-	nC



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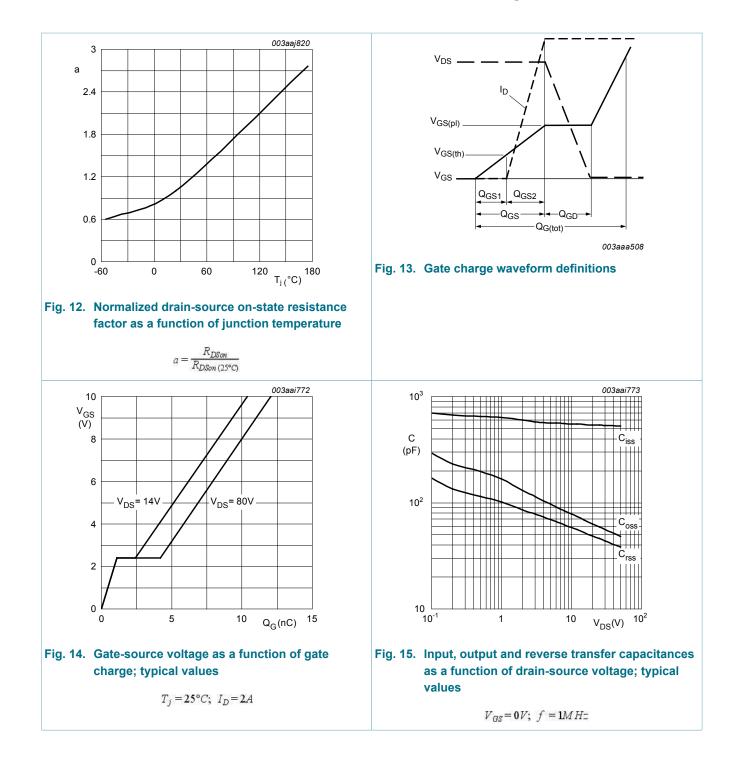
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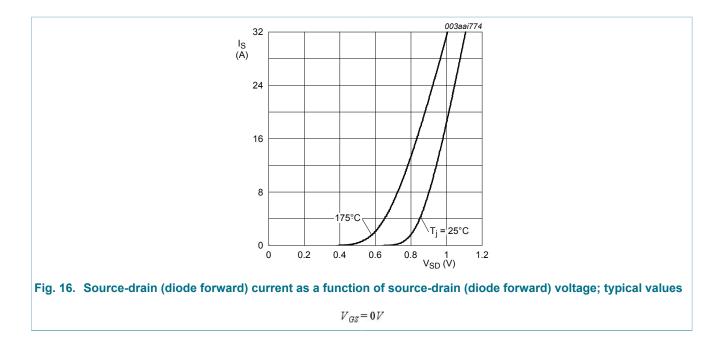
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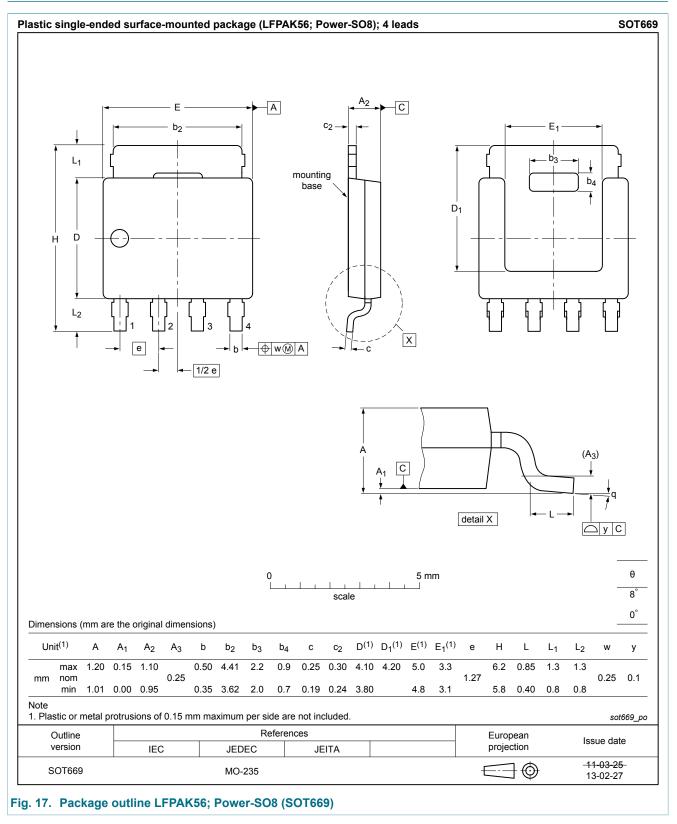
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11. Package outline



BUK9Y153-100E

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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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